

Abstract of the Disclosure:

A method for manufacturing a trench capacitor includes the step of etching a shallow isolation trench in a two-step process flow. During a first etching step, an etch chemistry  
5 based on chlorine or bromine performs a highly selective etch for silicon. During a second step, the etch chemistry is based on  $\text{SiF}_4$  and  $\text{O}_2$  which rather equally etches polysilicon and the collar isolation. On top of the wafer, the deposition of silicon oxide on the hard mask predominates and avoids an  
10 erosion of the hard mask. On the bottom of the trench the conformal etching of polysilicon and collar isolation predominates. The method provides an economic process flow and is suitable for small feature sizes.

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